DMA20403

Silicon PNP epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For general amplification

■ Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: B9

■ Basic Part Number

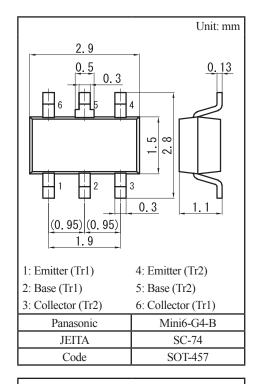
DSA2001 + DSA2002 (Individual)

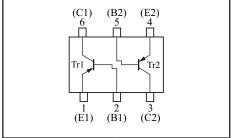
Packaging

DMA204030R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit	
Tr1	Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
	Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
	Emitter-base voltage (Collector open)	V _{EBO}	-7	V	
	Collector current	I_{C}	-100	mA	
	Peak collector current	I _{CP}	-200	mA	
Tr2	Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
	Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
	Emitter-base voltage (Collector open)	$V_{\rm EBO}$	-5	V	
	Collector current	I_{C}	-500	mA	
	Peak collector current	I _{CP}	-1	A	
Overall	Total power dissipation	P_{T}	300	mW	
	Junction temperature	T _j	150	°C	
	Operating ambient temperature	T _{opr}	-40 to +85	°C	
	Storage temperature	T _{stg}	-55 to +150	°C	





■ Electrical Characteristics $T_a = 25$ °C±3°C

• Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_{E} = 0$			-0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -10 \text{ V}, I_{B} = 0$			-100	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$		-0.2	-0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = -2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

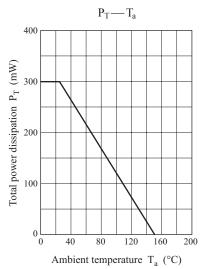
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_{E} = 0$			-0.1	μΑ
Forward current transfer ratio *1	h _{FE1}	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	120		340	
Forward current transfer ratio	h _{FE2}	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	40			_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.2	-0.6	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		- 0.9	-1.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -50 \text{ mA}$		130		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		7.3	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

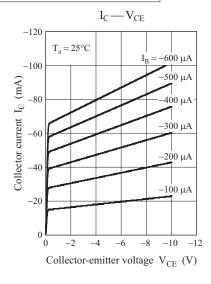
Common characteristics chart

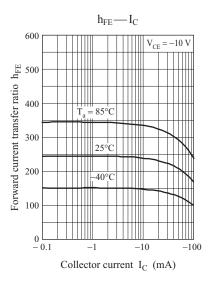


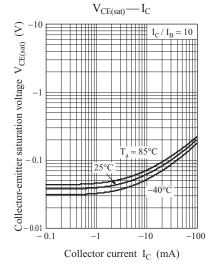
Ver. CED 2

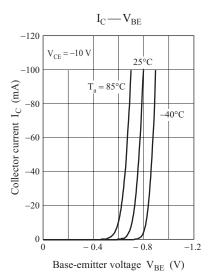
^{2. *1:} Pulse measurement

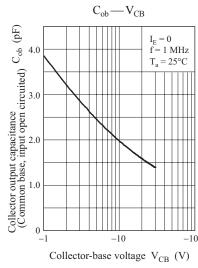
Characteristics charts of Tr1

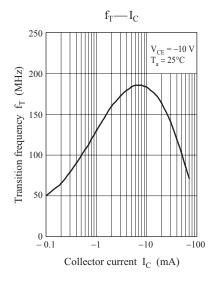




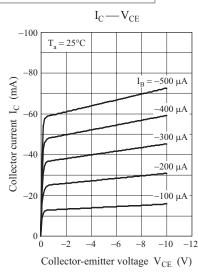


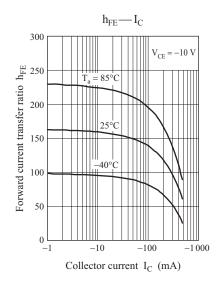


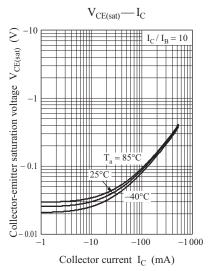




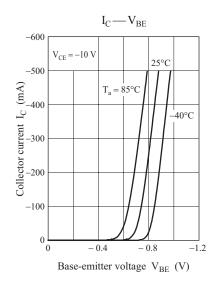
Characteristics charts of Tr2

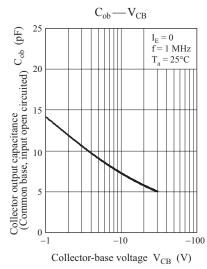


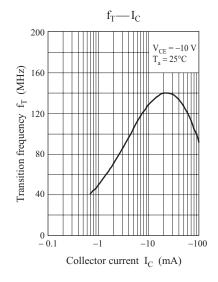




Ver. CED 3



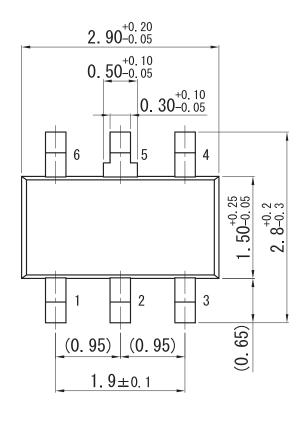


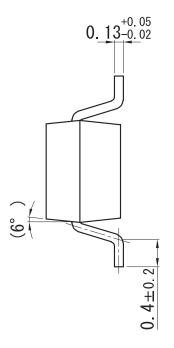


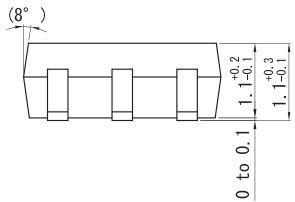
Ver. CED 4

Mini6-G4-B

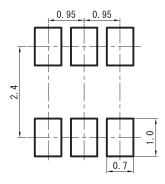
Unit: mm







■ Land Pattern (Reference) (Unit: mm)



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